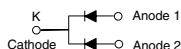




High Current Density Surface Mount Schottky Barrier Rectifiers



TO-277A (SMPC)



PRIMARY CHARACTERISTICS

| | |
|----------------------|------------|
| $I_{F(AV)}$ | 2 x 5.0 A |
| V_{RRM} | 30 V, 40 V |
| I_{FSM} | 200 A |
| E_{AS} | 20 mJ |
| V_F at $I_F = 5$ A | 0.37 V |
| T_J max. | 150 °C |

TYPICAL APPLICATIONS

For use in low voltage high frequency inverters, freewheeling, dc-to-dc converters, and polarity protection applications.

FEATURES

- Very low profile - typical height of 1.1 mm
- Ideal for automated placement
- Low forward voltage drop, low power losses
- High efficiency
- Low thermal resistance
- Meets MSL level 1, per J-STD-020
- Solder dip 265 °C max. 10 s, per JESD 22-A111
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC
- **Halogen-free according to IEC 61249-2-21 definition**



RoHS
COMPLIANT
HALOGEN
FREE

MECHANICAL DATA

Case: TO-277A (SMPC)

Molding compound meets UL 94 V-0 flammability rating

Base P/N-M3 - halogen-free and RoHS compliant, commercial grade

Base P/NHM3 - halogen-free and RoHS compliant, AEC-Q101 qualified

Terminals: Matte tin plated leads, solderable per J-STD-002 and JESD 22-B102

M3 suffix meets JESD 201 class 1A whisker test, HM3 suffix meets JESD 201 class 2 whisker test

MAXIMUM RATINGS ($T_A = 25$ °C unless otherwise noted)

| PARAMETER | SYMBOL | SS10P3C | SS10P4C | UNIT |
|---|----------------|---------------|---------|------|
| Device marking code | | S103C | S104C | |
| Maximum repetitive peak reverse voltage | V_{RRM} | 30 | 40 | V |
| Maximum average forward rectified current (Fig. 1) total device per diode | $I_{F(AV)}$ | 10 5.0 | | A |
| Peak forward surge current 10 ms single half sine-wave superimposed on rated load per diode | I_{FSM} | 200 | | A |
| Non-repetitive avalanche energy at 25 °C, $I_{AS} = 2$ A per diode | E_{AS} | 20 | | mJ |
| Operating junction and storage temperature range | T_J, T_{STG} | - 55 to + 150 | | °C |

SS10P3C & SS10P4C



Vishay General Semiconductor

| ELECTRICAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted) | | | | | | |
|--|------------------------|-------------------------|----------------|------|------|----------|
| PARAMETER | TEST CONDITIONS | | SYMBOL | TYP. | MAX. | UNIT |
| Instantaneous forward voltage per diode ⁽¹⁾ | I _F = 2.5 A | T _A = 25 °C | V _F | 0.40 | - | V |
| | I _F = 5.0 A | | | 0.45 | 0.53 | |
| | I _F = 2.5 A | T _A = 125 °C | | 0.29 | - | |
| | I _F = 5.0 A | | | 0.37 | 0.44 | |
| Reverse current per diode ⁽²⁾ | rated V _R | T _A = 25 °C | I _R | 56 | 550 | μA mA |
| | | T _A = 125 °C | | 28 | 45 | |
| Typical junction capacitance per diode | 4.0 V, 1 MHz | | C _J | 430 | - | pF |

Notes:

(1) Pulse test: 300 μs pulse width, 1 % duty cycle

(2) Pulse test: Pulse width ≤ 40 ms

| THERMAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted) | | | | |
|---|---------------------------------|---------|---------|------|
| PARAMETER | SYMBOL | SS10P3C | SS10P4C | UNIT |
| Typical thermal resistance per diode | R _{θJA} ⁽¹⁾ | 60 | | °C/W |
| | R _{θJL} | 3 | | |

Note:

(1) Units mounted on recommended P.C.B. 1 oz. pad layout

| ORDERING INFORMATION (Example) | | | | |
|--------------------------------|-----------------|------------------------|---------------|------------------------------------|
| PREFERRED P/N | UNIT WEIGHT (g) | PREFERRED PACKAGE CODE | BASE QUANTITY | DELIVERY MODE |
| SS10P4C-M3/86A | 0.10 | 86A | 1500 | 7" diameter plastic tape and reel |
| SS10P4C-M3/87A | 0.10 | 87A | 6500 | 13" diameter plastic tape and reel |
| SS10P4CHM3/86A ⁽¹⁾ | 0.10 | 86A | 1500 | 7" diameter plastic tape and reel |
| SS10P4CHM3/87A ⁽¹⁾ | 0.10 | 87A | 6500 | 13" diameter plastic tape and reel |

Note:

(1) AEC-Q101 qualified



RATINGS AND CHARACTERISTICS CURVES

($T_A = 25\text{ }^\circ\text{C}$ unless otherwise noted)

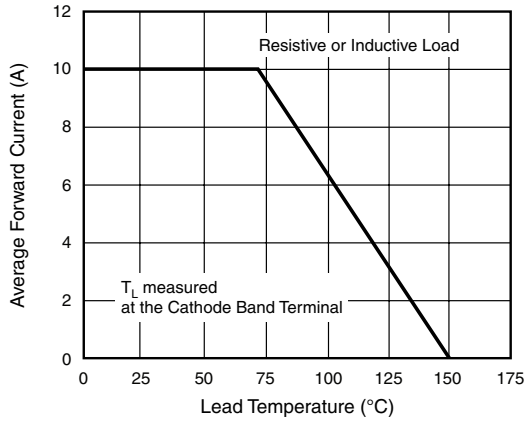


Figure 1. Maximum Forward Current Derating Curve

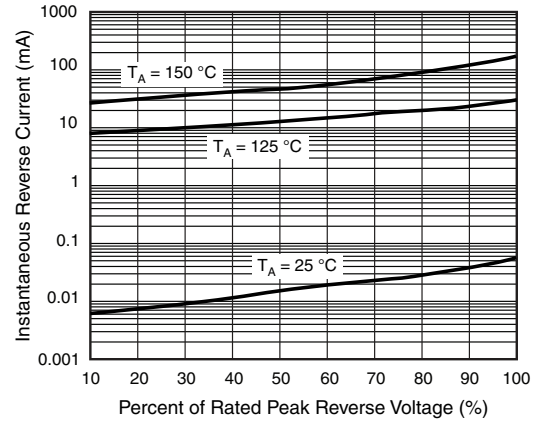


Figure 4. Typical Reverse Leakage Characteristics Per Diode

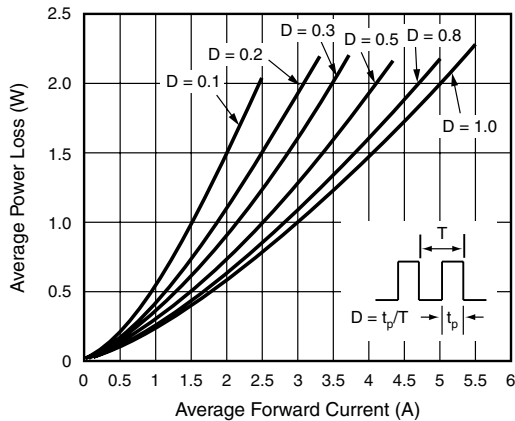


Figure 2. Forward Power Loss Characteristics Per Diode

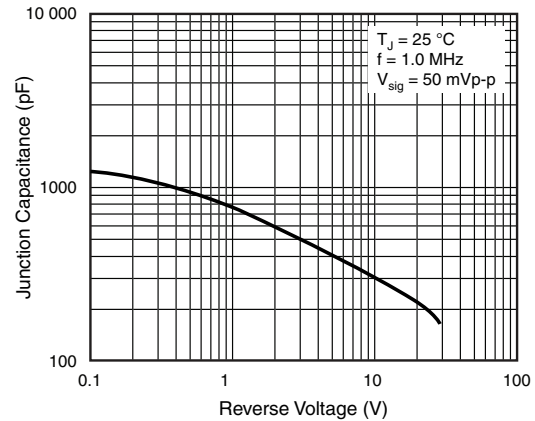


Figure 5. Typical Junction Capacitance Per Diode

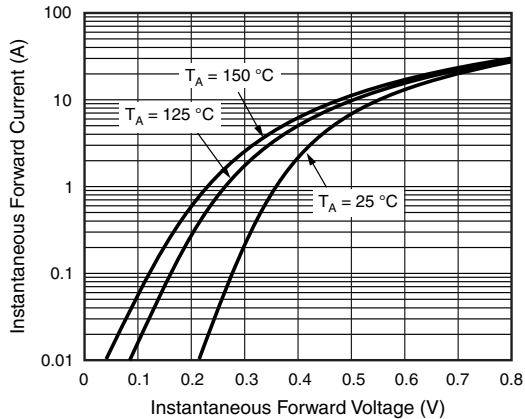


Figure 3. Typical Instantaneous Forward Characteristics Per Diode

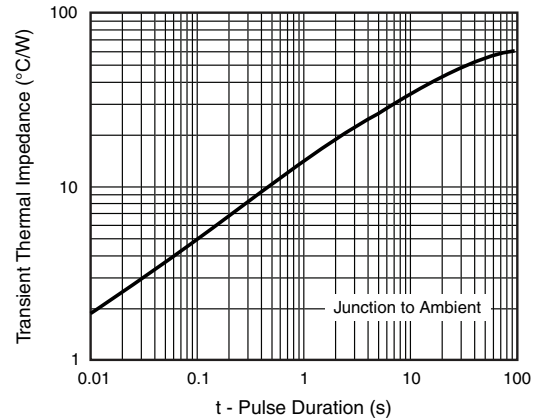


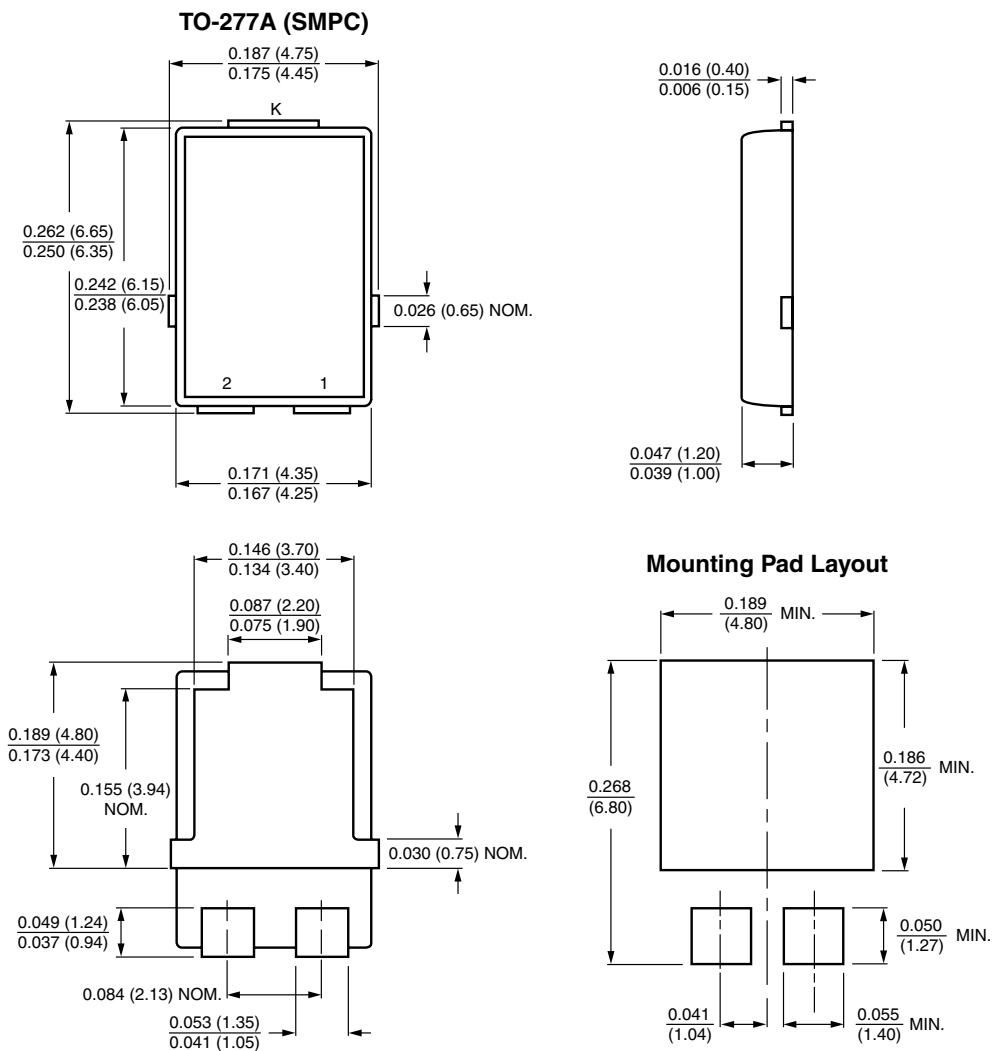
Figure 6. Typical Transient Thermal Impedance Per Diode

SS10P3C & SS10P4C

Vishay General Semiconductor



PACKAGE OUTLINE DIMENSIONS in inches (millimeters)



Conform to JEDEC TO-277A



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